

# Pawel Pfeffer

## List of Publications by Year in descending order

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58  
papers

1,666  
citations

394286

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citing authors

#	ARTICLE	IF	CITATIONS
1	Zero-field spin splitting in an inverted $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ heterostructure: Band nonparabolicity influence and the subband dependence. <i>Physical Review B</i> , 1999, 60, 7736-7739.	1.1	190
2	Spin splitting of conduction subbands in III-V heterostructures due to inversion asymmetry. <i>Physical Review B</i> , 1999, 59, R5312-R5315.	1.1	172
3	Conduction electrons in GaAs: Five-level $\mathbf{k}\cdot\mathbf{p}$ theory and polaron effects. <i>Physical Review B</i> , 1990, 41, 1561-1576.	1.1	167
4	Spin splitting of subband energies due to inversion asymmetry in semiconductor heterostructures. <i>Semiconductor Science and Technology</i> , 2004, 19, R1-R17.	1.0	158
5	Five-level $\mathbf{k}\cdot\mathbf{p}$ model for the conduction and valence bands of GaAs and InP. <i>Physical Review B</i> , 1996, 53, 12813-12828.	1.1	121
6	A study of the conduction band non-parabolicity, anisotropy and spin splitting in GaAs and InP. <i>Semiconductor Science and Technology</i> , 1987, 2, 568-577.	1.0	92
7	Spin splitting of conduction subbands in GaAs-Ga <sub>0.7</sub> Al <sub>0.3</sub> As heterostructures. <i>Physical Review B</i> , 1995, 52, R14332-R14335.	1.1	78
8	Non-parabolicity and anisotropy in the conduction band of GaAs. <i>Solid State Communications</i> , 1987, 61, 685-689.	0.9	62
9	Effect of inversion asymmetry on the conduction subbands in $\text{GaAs}_{1-x}\text{Al}_x$ heterostructures. <i>Physical Review B</i> , 1999, 59, 15902-15909.	1.1	50
10	Spin splitting of conduction energies in GaAs-Ga <sub>0.7</sub> Al <sub>0.3</sub> As heterojunctions at $B=0$ and $B\neq 0$ due to inversion asymmetry. <i>Physical Review B</i> , 1997, 55, R7359-R7362.	1.1	48
11	Five-level $\mathbf{k}\cdot\mathbf{p}$ model for conduction electrons in GaAs. Description of cyclotron resonance experiments. <i>Solid State Communications</i> , 1985, 53, 777-782.	0.9	42
12	Infrared magnetospectroscopy of GaAs at magnetic fields up to 150 T. <i>Physical Review B</i> , 1989, 40, 6189-6195.	1.1	42
13	Temperature dependence of the electron spin $g$ factor in GaAs. <i>Physical Review B</i> , 2008, 78, .	1.1	40
14	Theory of free-electron optical absorption in n-GaAs. <i>Solid State Communications</i> , 1984, 51, 179-183.	0.9	36
15	Bychkov-Rashba spin splitting and its dependence on magnetic field in $\text{InSb}/\text{In}_{0.91}\text{Al}_{0.09}\text{Sb}$ asymmetric quantum wells. <i>Physical Review B</i> , 2003, 68, .	1.1	30
16	Anisotropy of spin $g$ factor in $\text{GaAs}_{1-x}\text{Al}_x$ asymmetric quantum wells. <i>Physical Review B</i> , 2006, 74, .	1.1	30
17	Spin and cyclotron energies of electrons in $\text{GaAs}_{1-x}\text{Al}_x$ quantum wells. <i>Physical Review B</i> , 2006, 74, .	1.1	27
18	Resonant and nonresonant polarons in semiconductors. <i>Physical Review B</i> , 1988, 37, 2695-2698.	1.1	20

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19	Resonant magneto-polarons in bulk GaAs. Solid State Communications, 1986, 57, 847-851.	0.9	19
20	Theory of spin splitting in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ parabolic quantum wells controlled by an electric field. Physical Review B, 2005, 72, .	1.1	17
21	Tunable cyclotron resonance-laser in p-Ge. Semiconductor Science and Technology, 1992, 7, B604-B609.	1.0	16
22	Cyclotron resonance of conduction electrons in GaAs at very high magnetic fields. Physical Review B, 1997, 55, 13598-13604.	1.1	16
23	Observation of the zero-field spin splitting of the second subband in an inverted $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 767-770.	1.3	16
24	Infrared magnetospectroscopy of n-type InP at magnetic fields up to 150 T. Physical Review B, 1991, 44, 1087-1091.	1.1	14
25	GaAs as a narrow-gap semiconductor. Semiconductor Science and Technology, 1990, 5, S179-S181.	1.0	13
26	Pseudopotential and k.p band parameters for GaAs, InP and InSb. Semiconductor Science and Technology, 1991, 6, 963-968.	1.0	13
27	p-type Ge cyclotron-resonance laser: Theory and experiment. Physical Review B, 1993, 47, 4522-4531.	1.1	13
28	Experimental and theoretical study of magnetodons in GaAs and InP at megagauss fields. Physical Review B, 1994, 49, 1705-1710.	1.1	13
29	Average forces in bound and resonant quantum states. Physical Review B, 2001, 64, .	1.1	13
30	Anisotropy of the conduction band of InSb: Orbital and spin properties. Physical Review B, 1992, 46, 9469-9475.	1.1	11
31	Effective $g^*$ factor in the diluted nitrides $\text{Ga}_{1-y}\text{In}_y\text{N}_x\text{As}_{1-x}$ . Physical Review B, 2005, 71, .	1.1	11
32	Inelastic Scattering of Electrons by Optic Phonons in InSb $\epsilon$ -Type Semiconductors. Physica Status Solidi (B): Basic Research, 1978, 88, 247-260.	0.7	10
33	Interband Resonant Polarons in the Semimagnetic Zero-Gap Semiconductor $\text{Hg}_{1-x}\text{Mn}_x\text{Te}$ . Physical Review Letters, 1988, 61, 762-765.	2.9	9
34	Effects of spin splitting due to inversion asymmetry on magnetization and specific heat of 2D electron gas. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 533-537.	1.3	7
35	Temperature dependence of the electron spin $g$ factor in CdTe and InP. Journal of Applied Physics, 2012, 111, 083705.	1.1	7
36	High Intensity p-Ge Tunable Cyclotron Resonance Laser. Journal of Modern Optics, 1992, 39, 561-568.	0.6	5

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37	Influence of Barrier Material on Spin Splitting Due to Inversion Asymmetry in Heterostructures. Journal of Superconductivity and Novel Magnetism, 2003, 16, 351-354.	0.5	5
38	Resonant and nonresonant polarons in bulk InSb. Physical Review B, 1998, 57, 12156-12163.	1.1	4
39	Electrons in finite superlattices: soft and hard confinements. Semiconductor Science and Technology, 2009, 24, 105002.	1.0	4
40	Nernst-Ettingshausen effect at the trivial-nontrivial band ordering in topological crystalline insulator $\text{Pb}_{1-x}\text{Sn}_x\text{Se}$ . New Journal of Physics, 2016, 18, 013047.	1.2	4
41	Interband, intraband and spin-flip polarons in the zero-gap semiconductor $\text{Hg}_{1-x}\text{MnxTe}$ . Semiconductor Science and Technology, 1990, 5, S295-S298.	1.0	3
42	Spin transistors based on spatial control of electron spins in double quantum wells. Physical Review B, 2012, 86, .	1.1	3
43	Landau levels and shallow donor states in GaAs/AlGaAs multiple quantum wells at megagauss magnetic fields. Physical Review B, 2017, 95, .	1.1	3
44	Two-valence band electron and heat transport in monocrystalline PbTe-CdTe solid solutions with Cd content up to 10 atomic percent. Physical Review Materials, 2020, 4, .	0.9	3
45	Crossed-field hot-hole cyclotron resonance in p-Ge: nonparabolic and quantum effects. Semiconductor Science and Technology, 1993, 8, S313-S316.	1.0	2
46	Donors in GaAs and InP at megagauss fields. Physica B: Condensed Matter, 1994, 201, 288-291.	1.3	2
47	Theory of free-electron optical absorption in n-InSb.. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 117-118, 425-427.	0.9	1
48	Optical spin resonances due to structure and bulk inversion asymmetry in heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 392-395.	1.3	1
49	Electrons in GaAs/Ga $_{1-x}$ Al $_x$ As superlattices: Spin and orbital states in a magnetic field. Physical Review B, 2010, 81, .	1.1	1
50	The Klein Paradox in a Magnetic Field: Effects of Electron Spin. Acta Physica Polonica B, 2020, 51, 995.	0.3	1
51	Conduction Electrons in Bulk GaAs at High Magnetic Fields. Springer Series in Solid-state Sciences, 1987, , 523-530.	0.3	1
52	Insulator-metal transition in HgTe in crossed magnetic and electric fields. Semiconductor Science and Technology, 1993, 8, S161-S164.	1.0	0
53	Reply to "Comment on "Spin and cyclotron energies of electrons in GaAs/Ga $_{1-x}$ Al $_x$ As quantum wells". Physical Review B, 2007, 76, .	1.1	0
54	Jumping magneto-electric states of electrons in semiconductor multiple quantum wells. Semiconductor Science and Technology, 2011, 26, 085024.	1.0	0

#	ARTICLE	IF	CITATIONS
55	Oblique Reflection of Electrons from a Potential Barrier in Heterostructures. Acta Physica Polonica A, 2014, 126, 820-827.	0.2	0
56	Cyclotron and combined phonon-assisted resonances in the double-well heterostructure $\text{In}_{0.65}\text{Ga}_{0.35}\text{As}/\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ at megagauss magnetic fields. Physical Review B, 2018, 98, .	1.1	0
57	Controlled electron transmission by lead chalcogenide barrier potential. Semiconductor Science and Technology, 2021, 36, 045023.	1.0	0
58	Resonant Magneto-Polarons in InSb. Springer Series in Solid-state Sciences, 1992, , 633-636.	0.3	0